

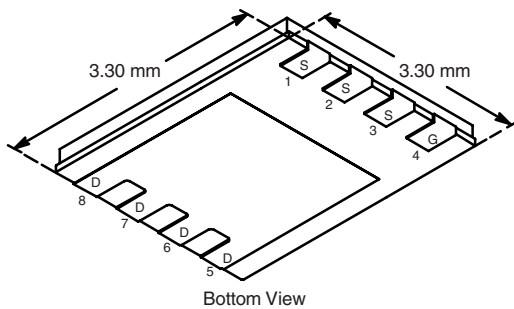


## P-Channel 30 V (D-S) MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)	$Q_g$ (Typ.)
- 30	0.007 at $V_{GS} = -10$ V	- 35 <sup>d</sup>	39.5 nC
	0.011 at $V_{GS} = -4.5$ V	- 35 <sup>d</sup>	

PowerPAK® 1212-8



Ordering Information: Si7625DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

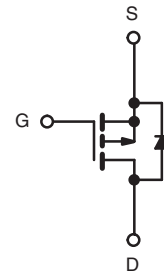
### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100%  $R_g$  Tested
- 100% UIS Tested
- Compliant to RoHS Directive 2002/95/EC


 RoHS  
 COMPLIANT  
 HALOGEN  
 FREE

### APPLICATIONS

- Notebook Adapter Switch
- Notebook Load Switch



P-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	- 30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150$ °C)	$I_D$	$T_C = 25$ °C	- 35 <sup>d</sup>
		$T_C = 70$ °C	- 35 <sup>d</sup>
		$T_A = 25$ °C	- 17.3 <sup>a, b</sup>
		$T_A = 70$ °C	- 13.8 <sup>a, b</sup>
Pulsed Drain Current	$I_{DM}$	- 80	A
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25$ °C	- 35 <sup>d</sup>
		$T_A = 25$ °C	- 3.0 <sup>a, b</sup>
Avalanche Current	$I_{AS}$	- 20	mJ
Single-Pulse Avalanche Energy	$E_{AS}$	20	
Maximum Power Dissipation	$P_D$	$T_C = 25$ °C	52
		$T_C = 70$ °C	33
		$T_A = 25$ °C	3.7 <sup>a, b</sup>
		$T_A = 70$ °C	2.4 <sup>a, b</sup>
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) <sup>e, f</sup>		260	

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a, c</sup>	$R_{thJA}$	26	33	°C/W
Maximum Junction-to-Case	$R_{thJC}$	1.9	2.4	

#### Notes:

- Surface mounted on 1" x 1" FR4 board.
- $t = 10$  s.
- Maximum under steady state conditions is 81 °C/W.
- Package limited.
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

## Si7625DN

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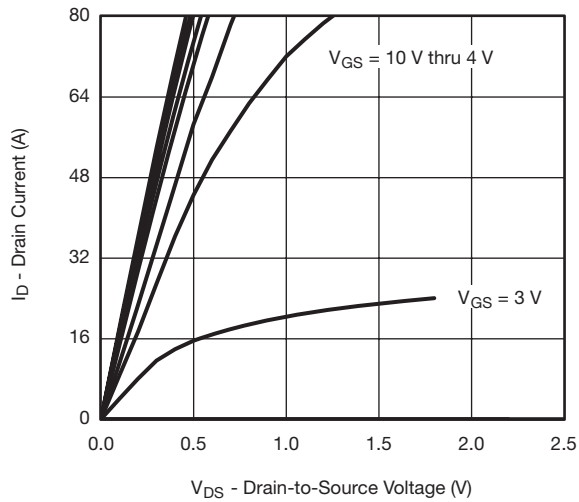
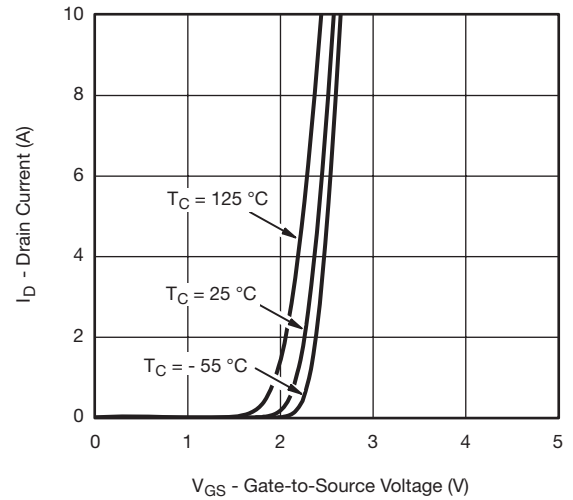
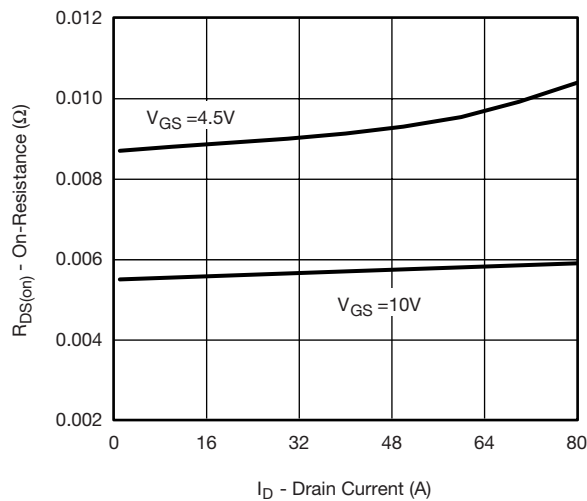
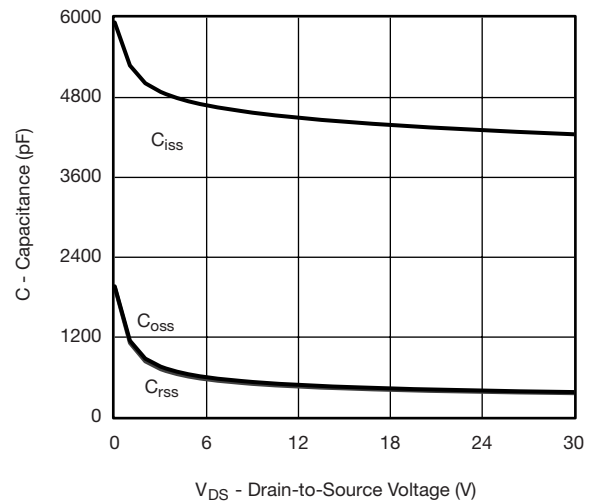
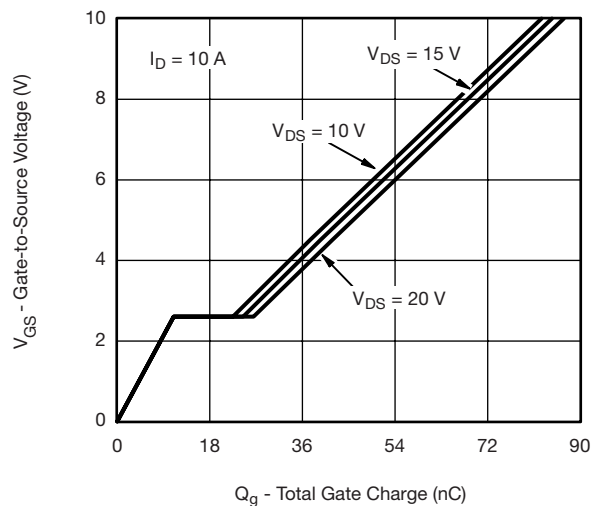
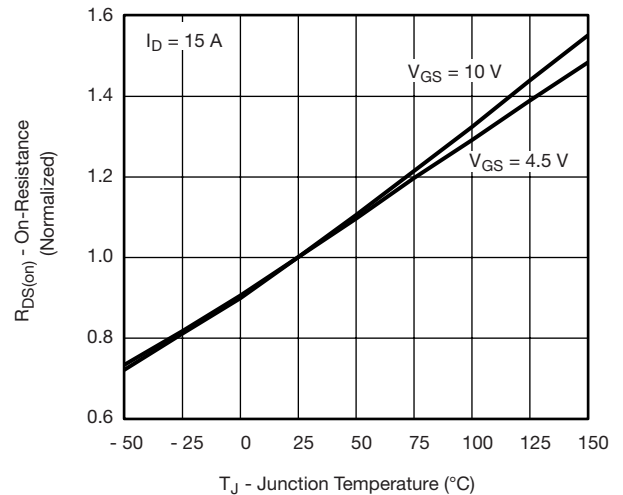


SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 μA	- 30			V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = - 250 μA		- 23		mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>			5.0		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 1.0		- 2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V			- 1	μA
		V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			- 5	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ - 10 V, V <sub>GS</sub> = - 10 V	- 30			A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 15 A		0.0056	0.007	Ω
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 10 A		0.0088	0.011	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 15 A		47		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz		4427		pF
Output Capacitance	C <sub>oss</sub>			452		
Reverse Transfer Capacitance	C <sub>rss</sub>			430		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 10 A		84.5	126	nC
		V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 10 A		39.5	60	
Q <sub>gs</sub>			11			
Q <sub>gd</sub>			13.5			
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.4	1.8	3.6	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = - 15 V, R <sub>L</sub> = 1.5 Ω I <sub>D</sub> ≡ - 10 A, V <sub>GEN</sub> = - 10 V, R <sub>g</sub> = 1 Ω		15	30	ns
Rise Time	t <sub>r</sub>			13	26	
Turn-Off DelayTime	t <sub>d(off)</sub>			55	100	
Fall Time	t <sub>f</sub>			10	20	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = - 15 V, R <sub>L</sub> = 1.5 Ω I <sub>D</sub> ≡ - 10 A, V <sub>GEN</sub> = - 4.5 V, R <sub>g</sub> = 1 Ω		55	100	
Rise Time	t <sub>r</sub>			42	80	
Turn-Off DelayTime	t <sub>d(off)</sub>			52	100	
Fall Time	t <sub>f</sub>			17	34	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 35	A
Pulse Diode Forward Current	I <sub>SM</sub>				- 80	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 3 A, V <sub>GS</sub> = 0 V		- 0.74	- 1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 10 A, dI/dt = 100 A/μs, T <sub>J</sub> = 25 °C		14	24	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			4	8	nC
Reverse Recovery Fall Time	t <sub>a</sub>			8		ns
Reverse Recovery Rise Time	t <sub>b</sub>			6		

Notes:

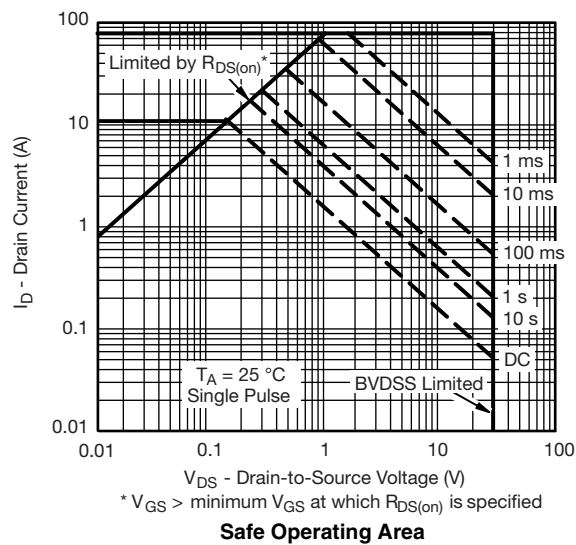
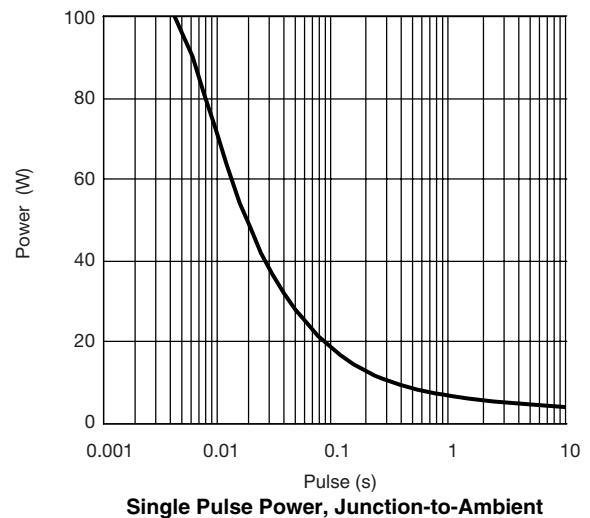
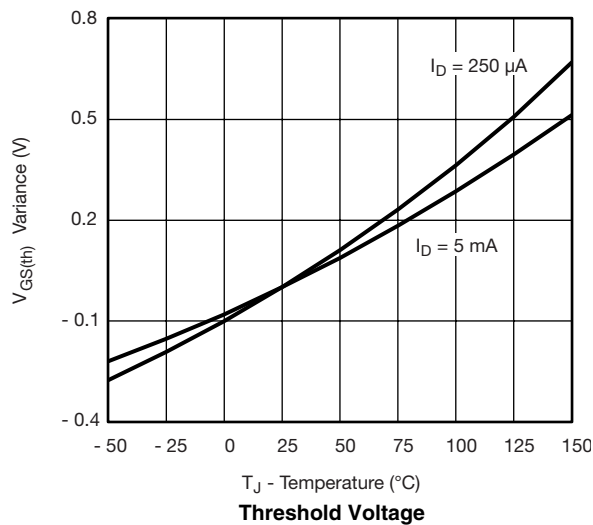
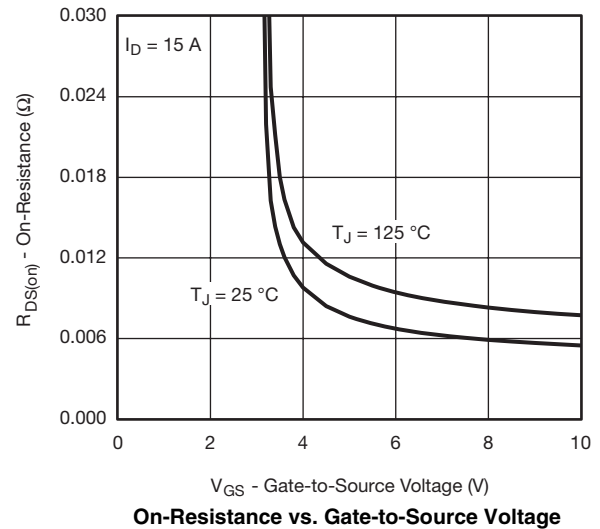
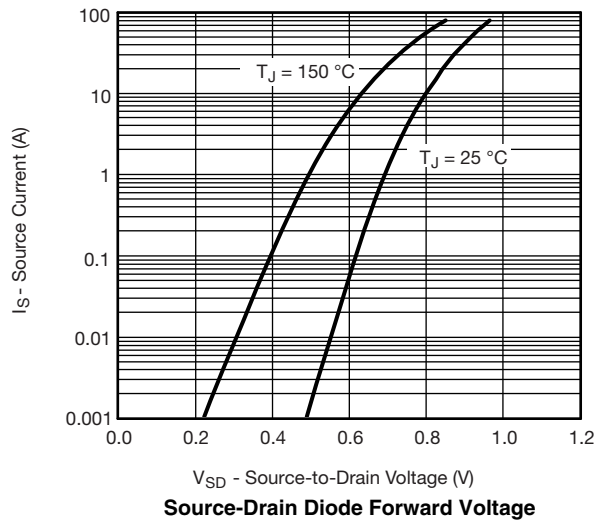
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

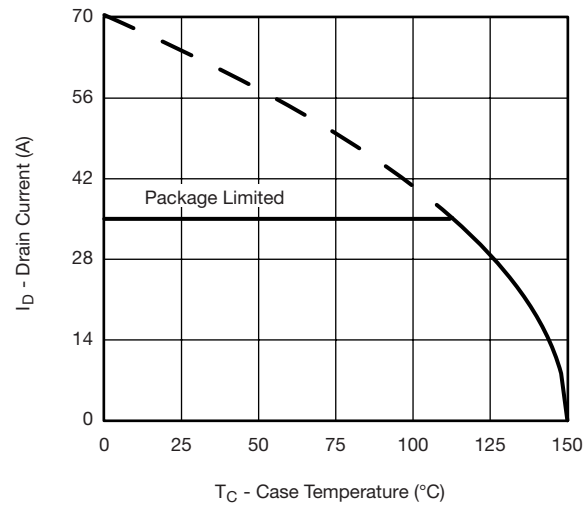
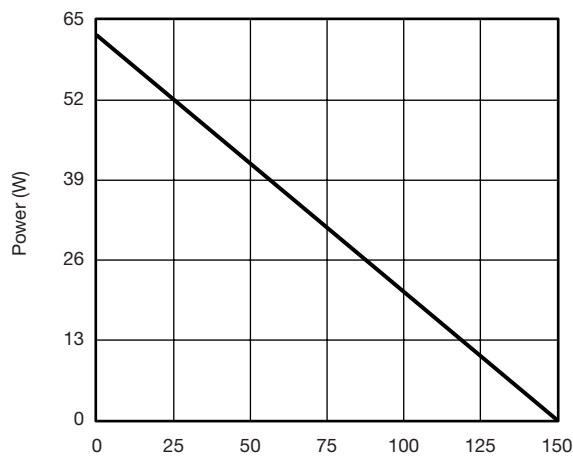
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.


**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

**Output Characteristics**

**Transfer Characteristics**

**On-Resistance vs. Drain Current**

**Capacitance**

**Gate Charge**

**On-Resistance vs. Junction Temperature**

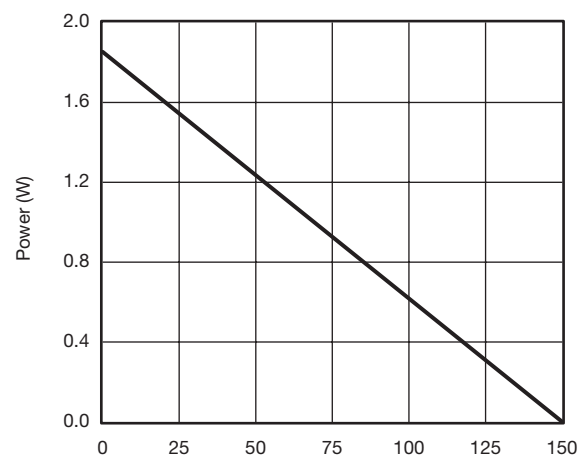
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**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

**MOSFET TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Current Derating\***

$T_C$  - Case Temperature (°C)  
**Power, Junction-to-Case**

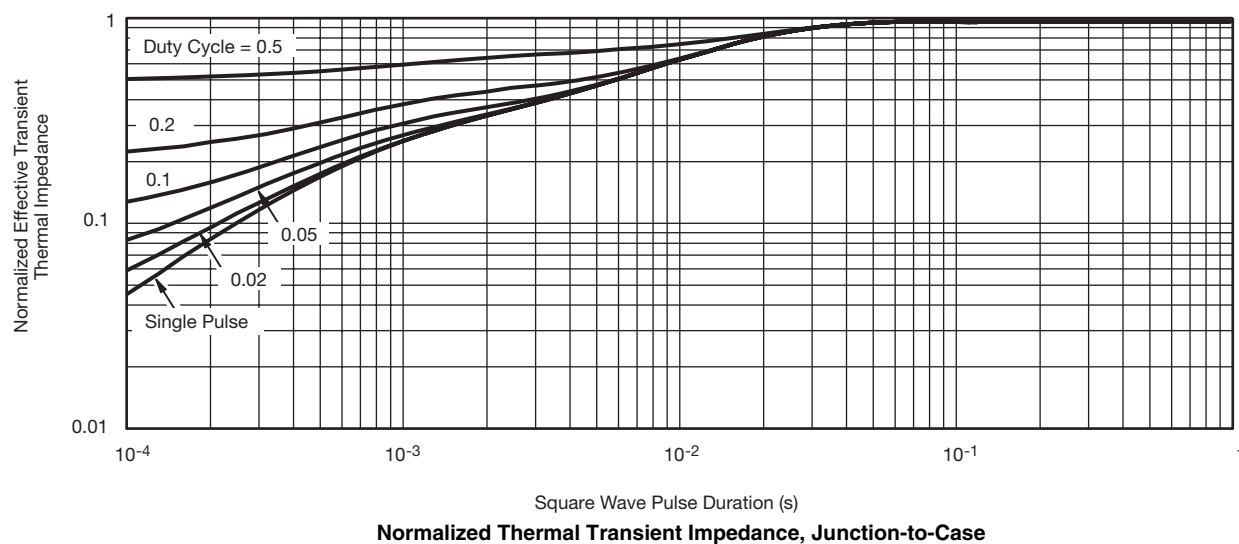
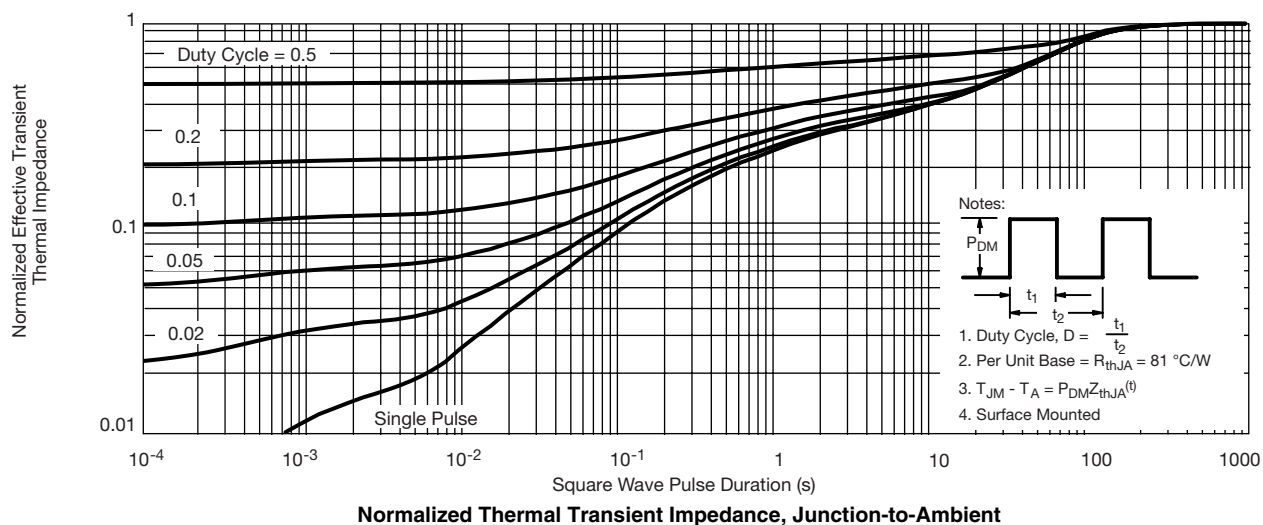


$T_A$  - Ambient Temperature (°C)  
**Power, Junction-to-Ambient**

\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?65737](http://www.vishay.com/ppg?65737).



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